

Discrete color centers in two-dimensional hexagonal boron nitride induced by fast neutron irradiation

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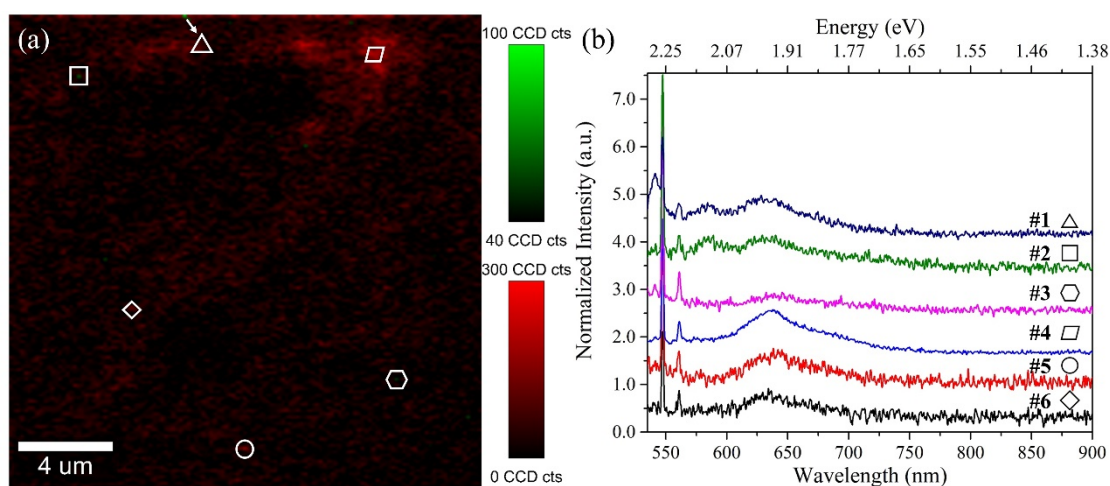


Figure S1: (a) A 2D spatial map of PL integrated intensity of an untreated sample. The green and red colors were corresponding to the integral intervals within 567.5-592.5 nm and 610-650 nm, respectively. PL spectra of selected points were shown in (b), corresponding to the points marked in (a).

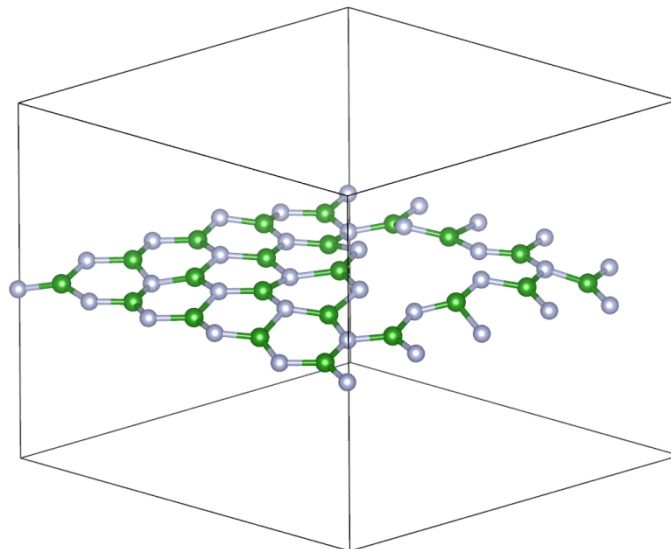


Figure S2: ab-initio molecular dynamics simulation of V_{B3NI} , which was taken on the defect supercell for 300 steps with time step of 3fs at 1000 K. The corresponding video of the simulation result can be found in the supplementary information Video S1.